

<IGBT Modules>

CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

TX		Collector current I_C 1 0 0 A Collector-emitter voltage V_{CES} 1 7 0 0 V Maximum junction temperature T_{vjmax} 1 7 5 °C •Flat base type •Copper base plate (Nickel-plating) •RoHS Directive compliant •Tin-plating pin terminals
TXP		Collector current I_C 1 0 0 A Collector-emitter voltage V_{CES} 1 7 0 0 V Maximum junction temperature T_{vjmax} 1 7 5 °C •Flat base type •Copper base plate (Nickel-plating) •RoHS Directive compliant •Tin-plating pressfit terminals
sixpack (three-phase bridge)		•UL Recognized under UL1557, File No. E323585

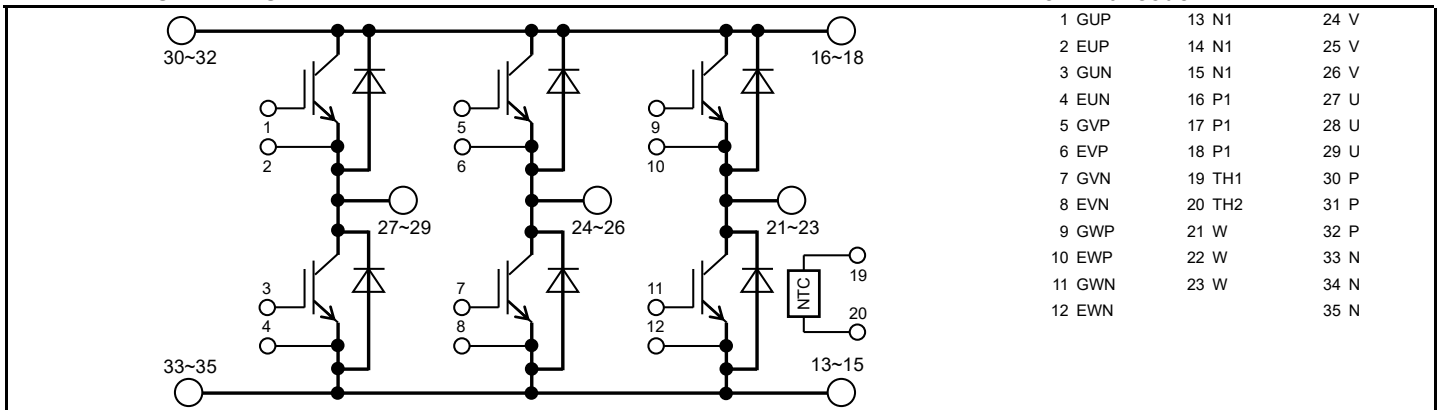
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OPTION (Below options are available.)

- PC-TIM (Phase Change Thermal Interface Material) pre-apply (Note10)

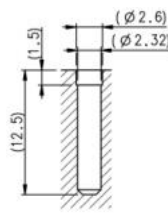
INTERNAL CONNECTION



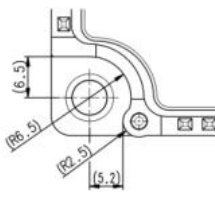
OUTLINE DRAWING

COM.

SECTION A



MOUNTING HOLES



Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

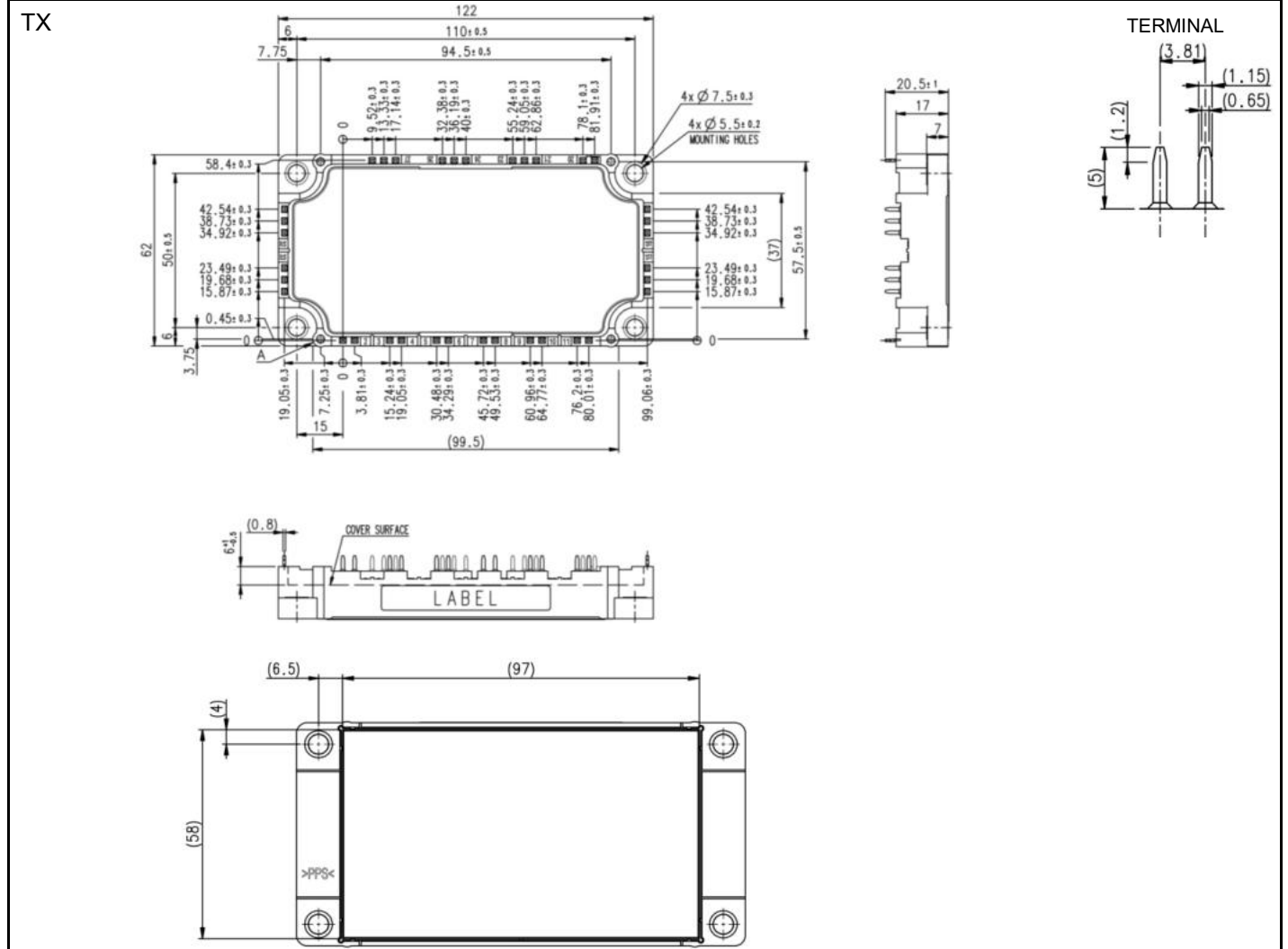
CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE

INSULATED TYPE

OUTLINE DRAWING

Dimension in mm

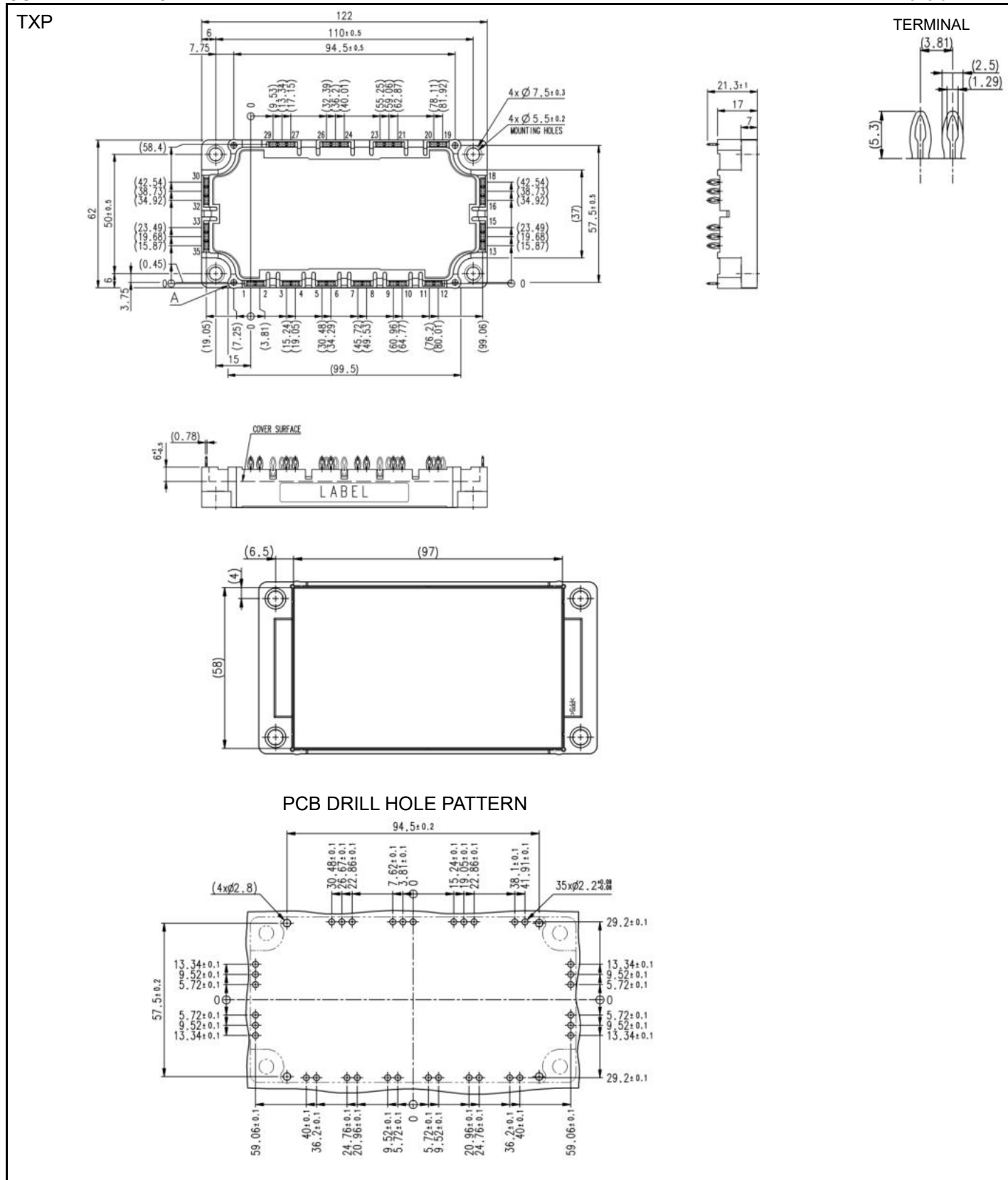


CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

OUTLINE DRAWING

Dimension in mm



CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1700	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=98\text{ }^{\circ}\text{C}$ (Note2, 4)	100	A
I_{CRM}		Pulse, Repetitive (Note3)	200	
P_{tot}	Total power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note2, 4)	590	W
I_E (Note1)	Emitter current	DC (Note2)	100	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	200	

MODULE

Symbol	Item	Conditions	Rating	Unit
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
T_{vjmax}	Maximum junction temperature	Instantaneous event (overload) (Note10)	175	$^{\circ}\text{C}$
T_{Cmax}	Maximum case temperature	(Note4, 10)	125	
T_{vjop}	Operating junction temperature	Continuous operation (under switching) (Note10)	-40 ~ +150	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited		-	-	1.0	mA
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited		-	-	0.5	μA
V _{GE(th)}	Gate-emitter threshold voltage	I _C =10 mA, V _{CE} =10 V		5.4	6.0	6.6	V
V _{CESat} (Terminal)	Collector-emitter saturation voltage	I _C =100 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	2.00	2.40	V
			T _{vj} =125 °C	-	2.40	-	
			T _{vj} =150 °C	-	2.50	-	
V _{CESat} (Chip)		I _C =100 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	-	1.95	2.35	V
			T _{vj} =125 °C	-	2.35	-	
			T _{vj} =150 °C	-	2.45	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited		-	-	26.7	nF
C _{oes}	Output capacitance			-	-	0.7	
C _{res}	Reverse transfer capacitance			-	-	0.2	
Q _G	Gate charge	V _{CC} =1000 V, I _C =100 A, V _{GE} =15 V		-	0.78	-	μC
t _{d(on)}	Turn-on delay time	V _{CC} =1000 V, I _C =100 A, V _{GE} =±15 V, R _G =0 Ω, Inductive load		-	-	800	ns
t _r	Rise time			-	-	200	
t _{d(off)}	Turn-off delay time			-	-	800	
t _f	Fall time			-	-	600	
V _{EC} (Note1) (Terminal)	Emitter-collector voltage	I _E =100 A, G-E short-circuited, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	2.70	3.30	V
			T _{vj} =125 °C	-	2.90	-	
			T _{vj} =150 °C	-	2.90	-	
V _{EC} (Note1) (Chip)			I _E =100 A, G-E short-circuited, (Note5)	T _{vj} =25 °C	-	2.65	3.25
		T _{vj} =125 °C		-	2.75	-	
		T _{vj} =150 °C		-	2.75	-	
t _{rr} (Note1)	Reverse recovery time	V _{CC} =1000 V, I _E =100 A, V _{GE} =±15 V, R _G =0 Ω, Inductive load		-	-	300	ns
Q _{rr} (Note1)	Reverse recovery charge			-	3.4	-	μC
E _{on}	Turn-on switching energy per pulse	V _{CC} =1000 V, I _C =I _E =100 A,		-	30.8	-	mJ
E _{off}	Turn-off switching energy per pulse	V _{GE} =±15 V, R _G =0 Ω, T _{vj} =150 °C,		-	29.8	-	
E _{rr} (Note1)	Reverse recovery energy per pulse	Inductive load		-	9.4	-	mJ
R _{CC'+EE'}	Internal lead resistance	Main terminals-chip, per switch, T _C =25 °C (Note4)		-	1.8	-	mΩ
r _g	Internal gate resistance	Per switch		-	7.5	-	Ω

ELECTRICAL CHARACTERISTICS (cont.: $T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)**NTC THERMISTOR PART**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	4.85	5.00	5.15	k Ω
$\Delta R/R$	Deviation of resistance	$R_{100}=493\text{ }\Omega$, $T_C=100\text{ }^{\circ}\text{C}$ (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	254	K/kW
$R_{th(j-c)D}$		Junction to case, per Inverter FWD (Note4)	-	-	429	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, Thermal grease applied (Note4, 7, 10)	-	11.5	-	K/kW
		per 1 module PC-TIM applied (Note4, 8, 10)	-	3.1	-	

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
d_s	Creepage distance	Solder pin type (TX)	Terminal to terminal		16.4	mm
			Terminal to base plate		18.5	
		Pressfit pin type (TXP)	Terminal to terminal		19.0	mm
			Terminal to base plate		18.6	
d_a	Clearance	Solder pin type (TX)	Terminal to terminal		10.2	mm
			Terminal to base plate		9.0	
		Pressfit pin type (TXP)	Terminal to terminal		8.9	mm
			Terminal to base plate		9.0	
e_c	Flatness of base plate	On the centerline X, Y (Note9)	± 0	-	+200	μm
m	mass	-	-	270	-	g

*. This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU) 2015/863.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

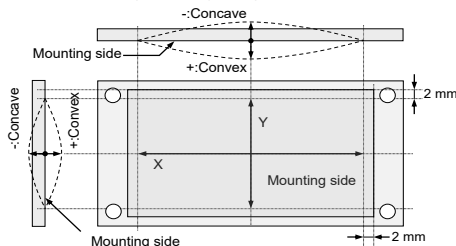
- Junction temperature (T_{vj}) should not increase beyond $T_{vj\max}$ rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed $T_{vj\max}$ rating.
- Case temperature (T_C) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.
Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

$$6. B_{(25/50)} = \ln \left(\frac{R_{25}}{R_{50}} \right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}} \right)$$

R_{25} : resistance at absolute temperature T_{25} [K]; $T_{25}=25\text{ }^{\circ}\text{C}+273.15=298.15\text{ [K]}$

R_{50} : resistance at absolute temperature T_{50} [K]; $T_{50}=50\text{ }^{\circ}\text{C}+273.15=323.15\text{ [K]}$

- Typical value is measured by using thermally conductive grease of $\lambda=0.9\text{ W/(m}\cdot\text{K)}/D_{(C-S)}=50\text{ }\mu\text{m}$.
- Typical value is measured by using PC-TIM of $\lambda=3.4\text{ W/(m}\cdot\text{K)}/D_{(C-S)}=50\text{ }\mu\text{m}$.
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



- Long term performance related to thermal conductive grease and PC-TIM (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under your specific application conditions. Each temperature condition ($T_{vj\max}$, $T_{vj\text{op}}$, $T_{C\max}$) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.

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HIGH POWER SWITCHING USE
INSULATED TYPE

Note11. Use the following screws when mounting the printed circuit board (PCB) on the standoffs.

PCB thickness : t1.6

Type	Manufacturer	Size	Tightening torque (N·m)	Recommended tightening method
(1) PT®	EJOT	K25×8	0.55 ± 0.055	by handwork (equivalent to 30 rpm by mechanical screw driver) ~ 600 rpm (by mechanical screw driver)
(2) PT®		K25×10	0.75 ± 0.075	
(3) DELTA PT®		25×8	0.55 ± 0.055	
(4) DELTA PT®		25×10	0.75 ± 0.075	
(5) B1 tapping screw	-	φ2.6×10	0.75 ± 0.075	
		φ2.6×12		

RECOMMENDED OPERATING CONDITIONS

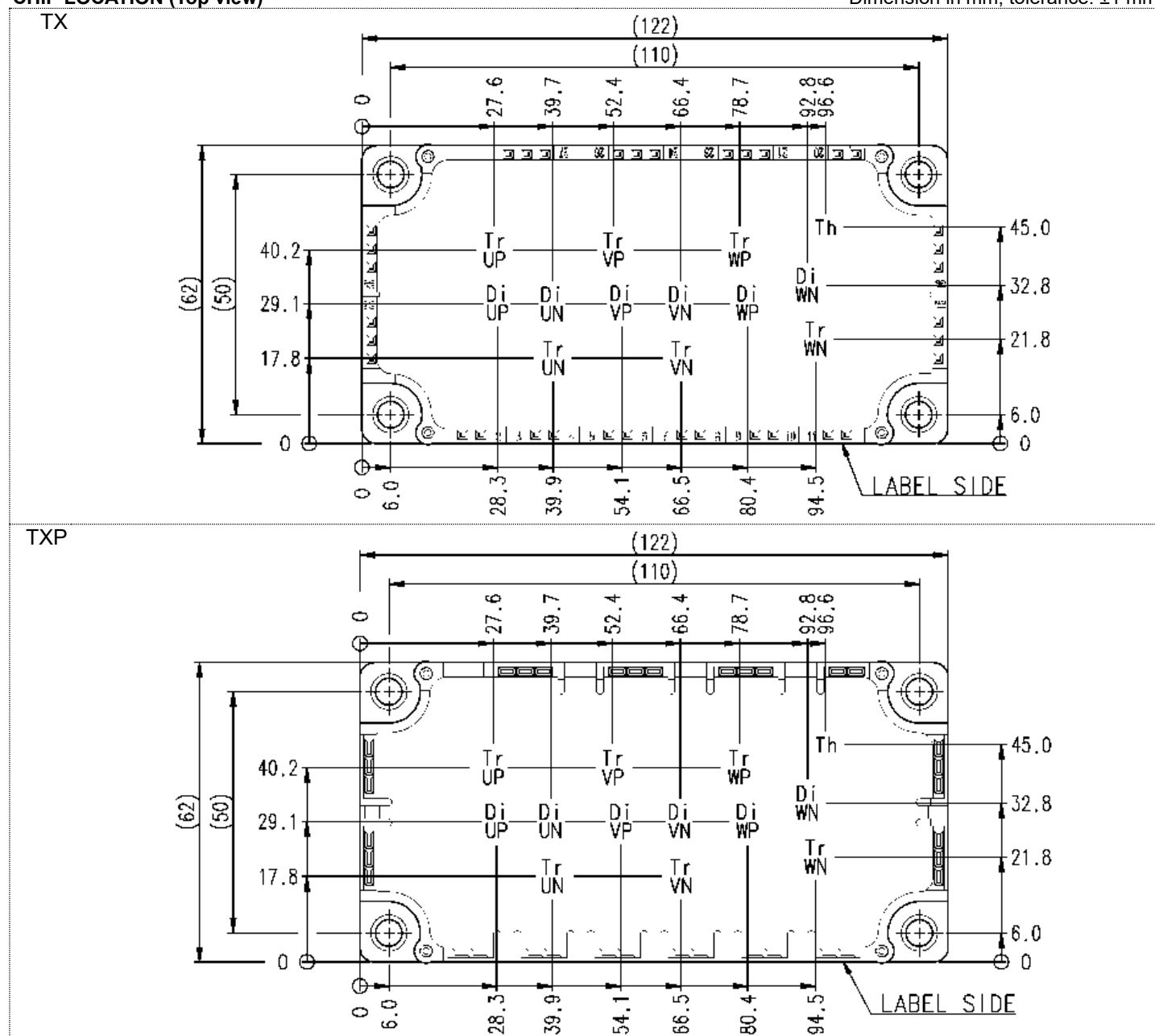
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across P-N terminals	-	1000	1200	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G*P-E*P/G*N-E*N terminals (*=U,V,W)	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	0	-	91	Ω

CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE

INSULATED TYPE

CHIP LOCATION (Top view)

Dimension in mm, tolerance: ± 1 mm

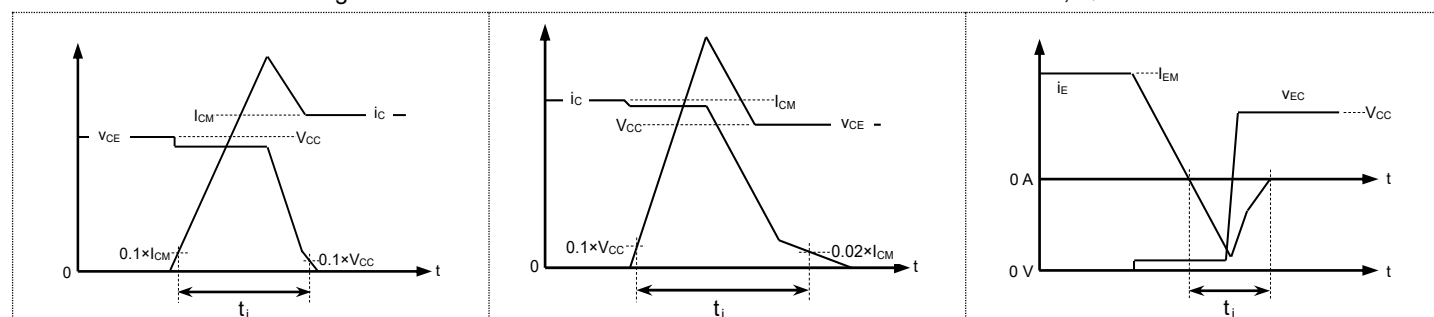
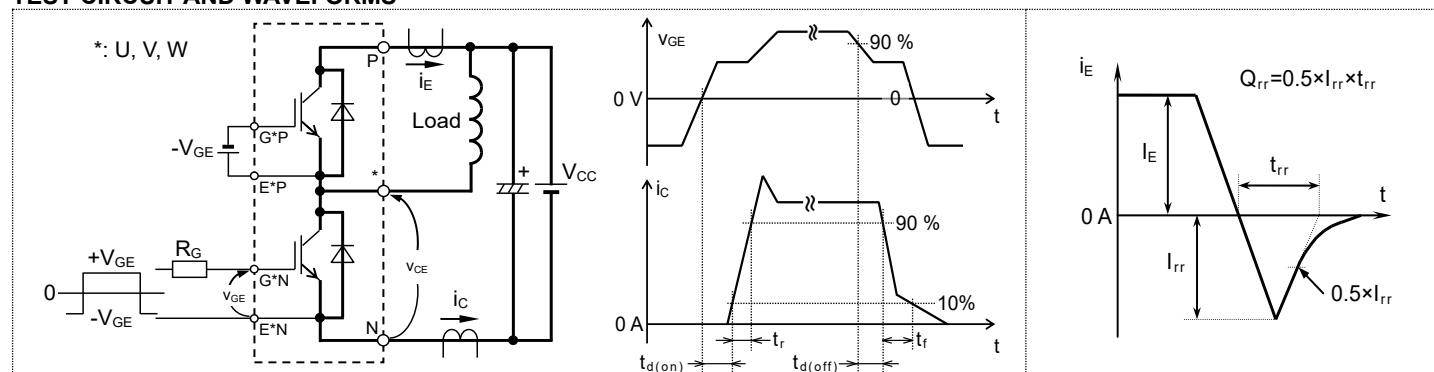
Tr*P/Tr*N: IGBT, Di*P/Di*N: FWD (*=U,V,W), Th: NTC thermistor

CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE

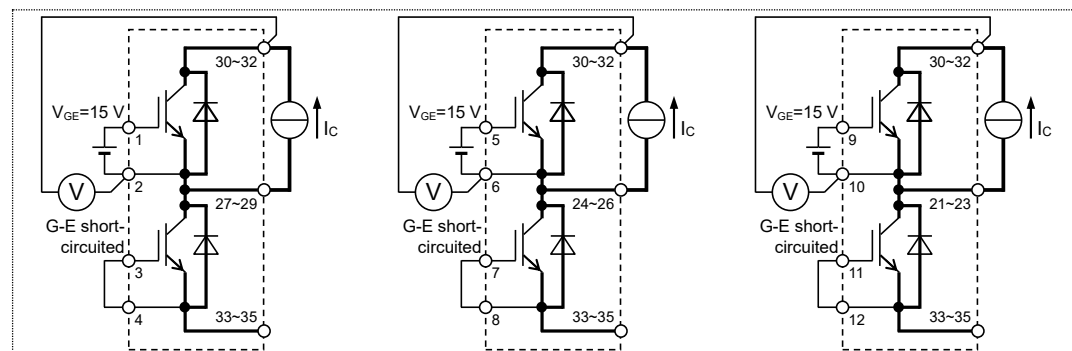
INSULATED TYPE

TEST CIRCUIT AND WAVEFORMS



Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

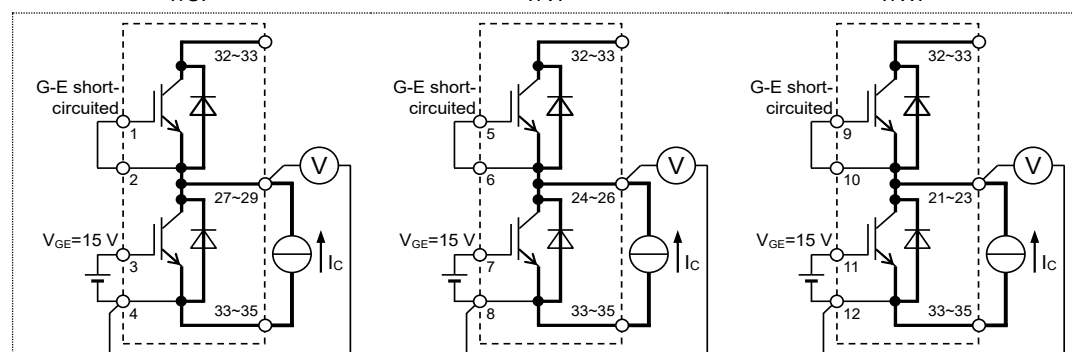
TEST CIRCUIT



TrUP

TrVP

TrWP



TrUN

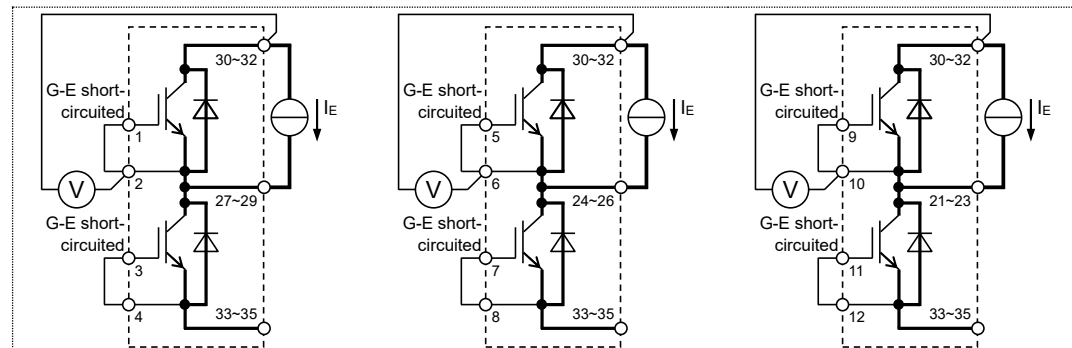
TrVN

TrWN

Gate-emitter GVP-EVP, GVN-EVN,
short-circuited GWP-EWP, GWN-EWN

Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GWP-EWP, GWN-EWN

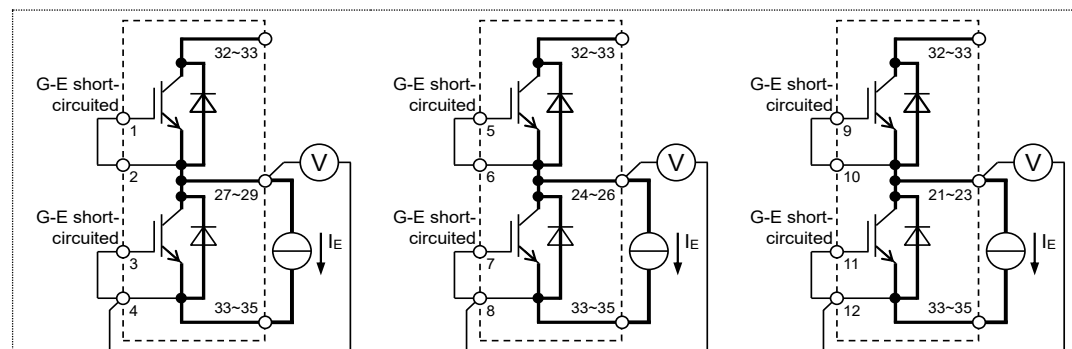
Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GVP-EVP, GVN-EVN

 V_{CEsat} characteristics test circuit

DiUP

DiVP

DiWP



DiUN

DiVN

DiWN

Gate-emitter GVP-EVP, GVN-EVN,
short-circuited GWP-EWP, GWN-EWN

Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GWP-EWP, GWN-EWN

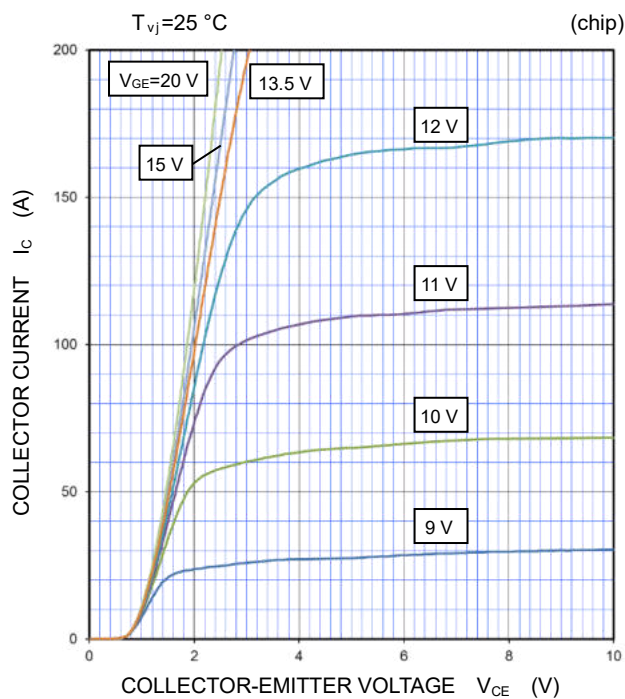
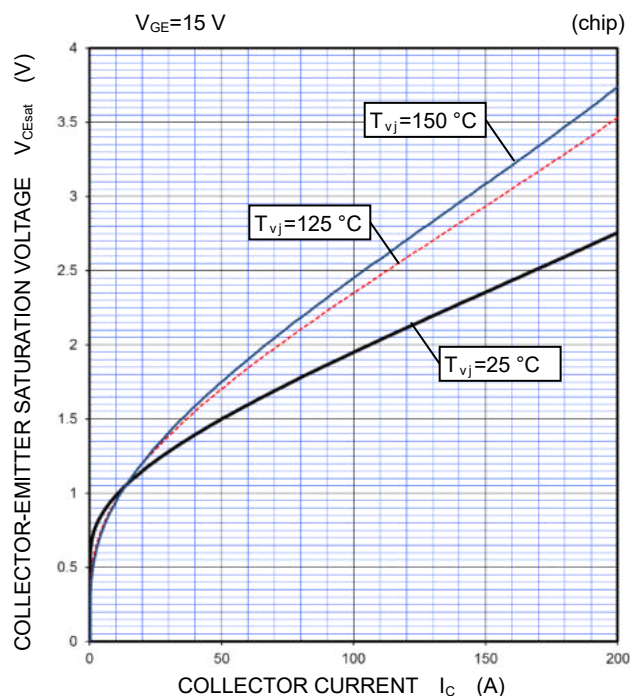
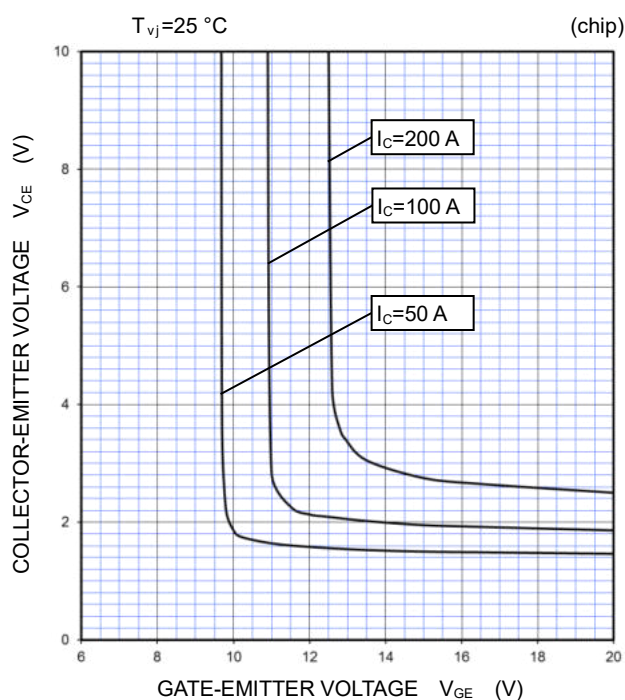
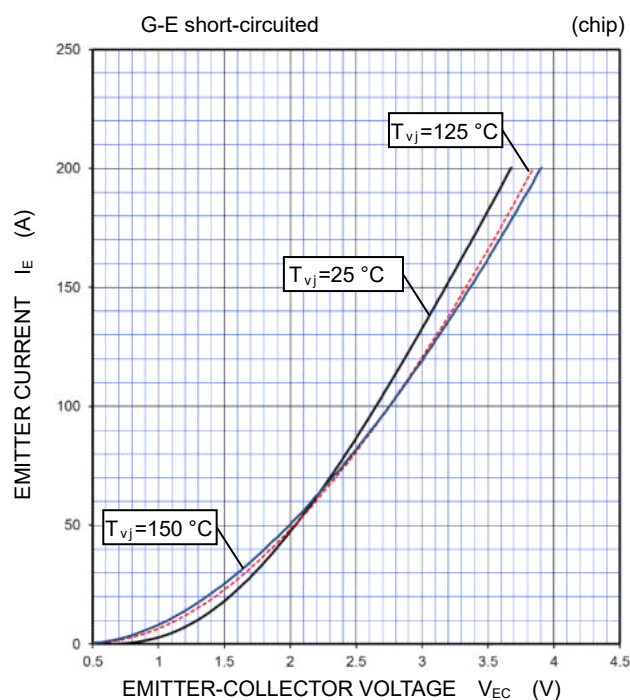
Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GVP-EVP, GVN-EVN

 V_{EC} characteristics test circuit

CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE

INSULATED TYPE

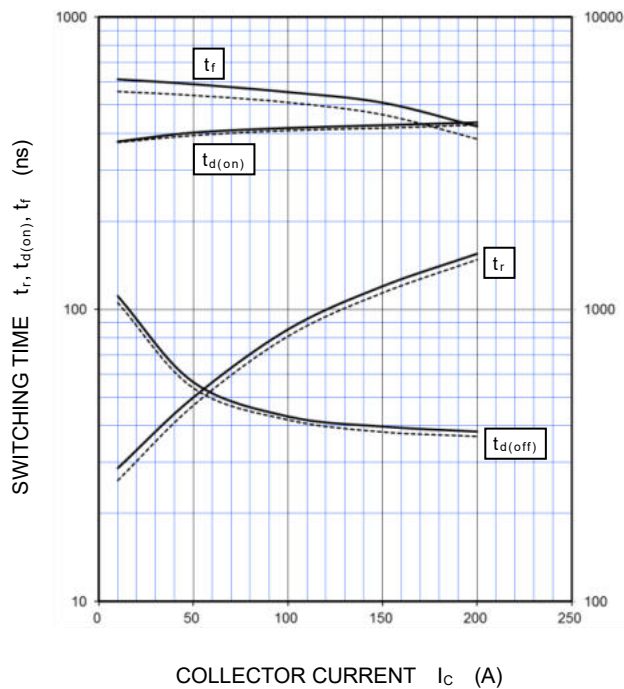
PERFORMANCE CURVES**INVERTER PART****OUTPUT CHARACTERISTICS
(TYPICAL)****COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)****COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS
(TYPICAL)****FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**

PERFORMANCE CURVES

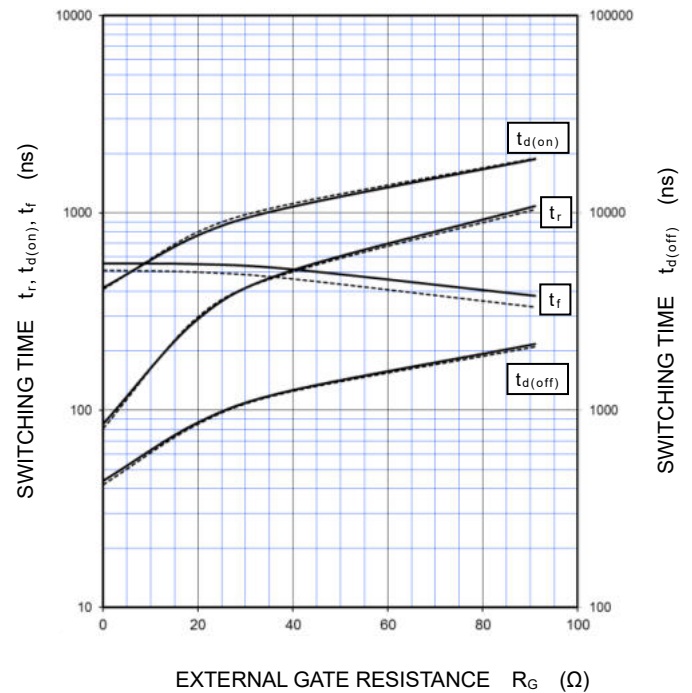
INVERTER PART

HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

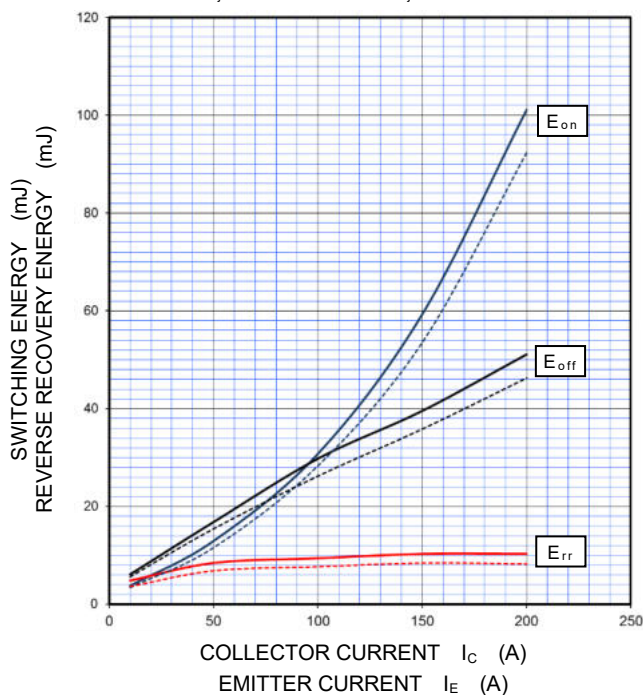
$V_{CC}=1000\text{ V}$, $R_G=0\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - - -: $T_{vj}=125\text{ }^\circ\text{C}$

HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

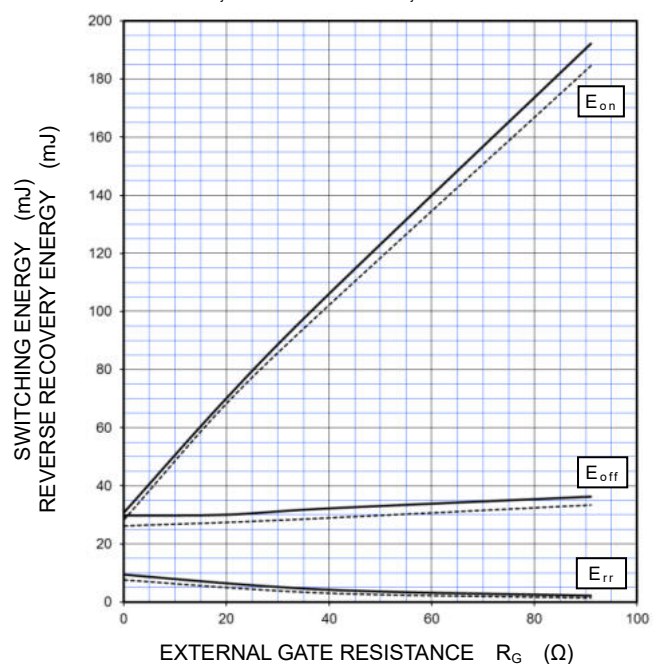
$V_{CC}=1000\text{ V}$, $I_C=100\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - - -: $T_{vj}=125\text{ }^\circ\text{C}$

HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=1000\text{ V}$, $R_G=0\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE

HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)

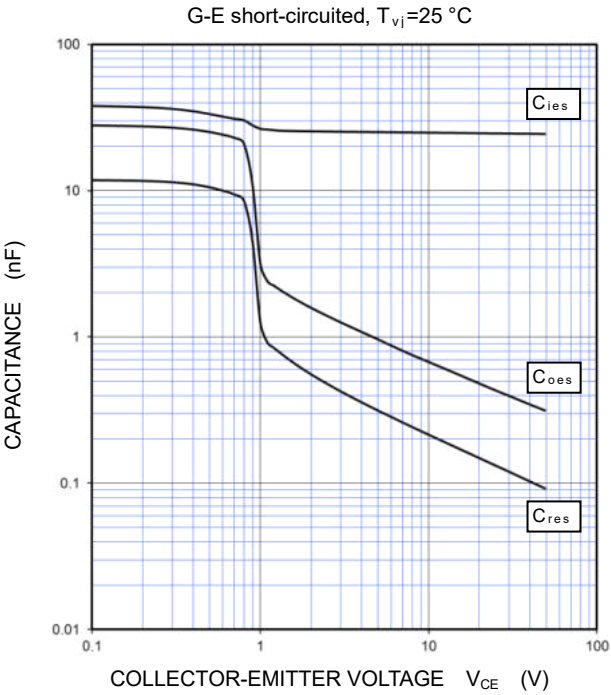
$V_{CC}=1000\text{ V}$, $I_C/I_E=100\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



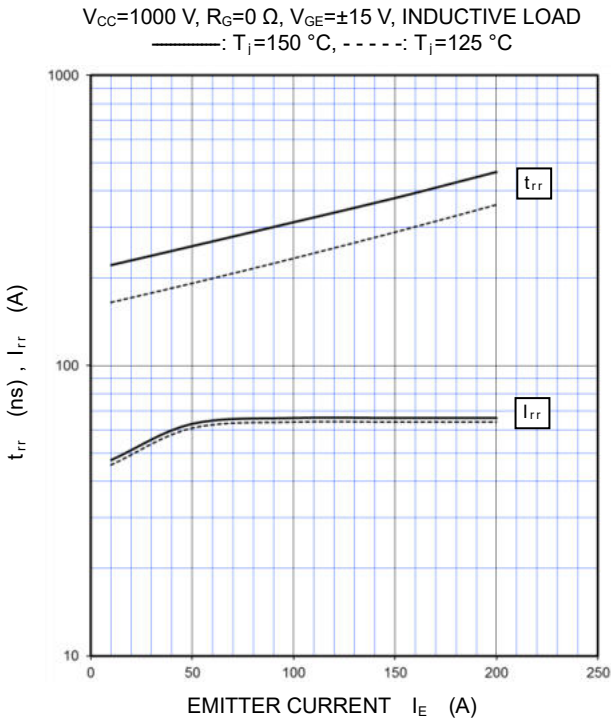
PERFORMANCE CURVES

INVERTER PART

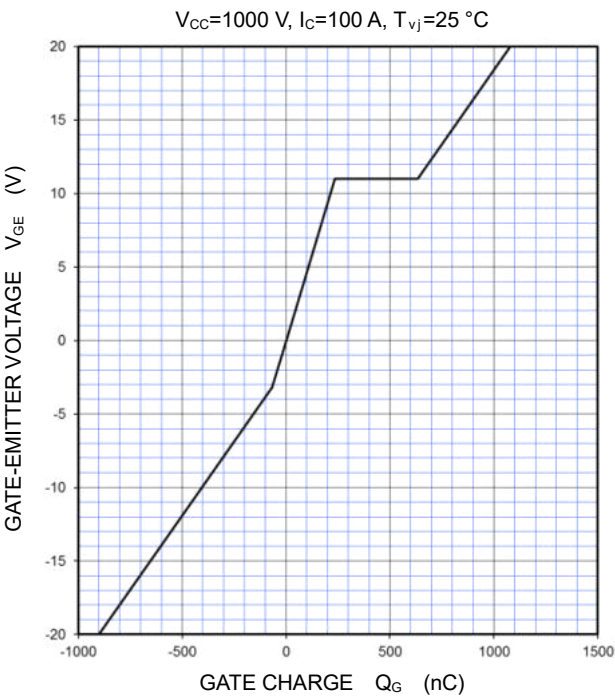
CAPACITANCE CHARACTERISTICS
(TYPICAL)



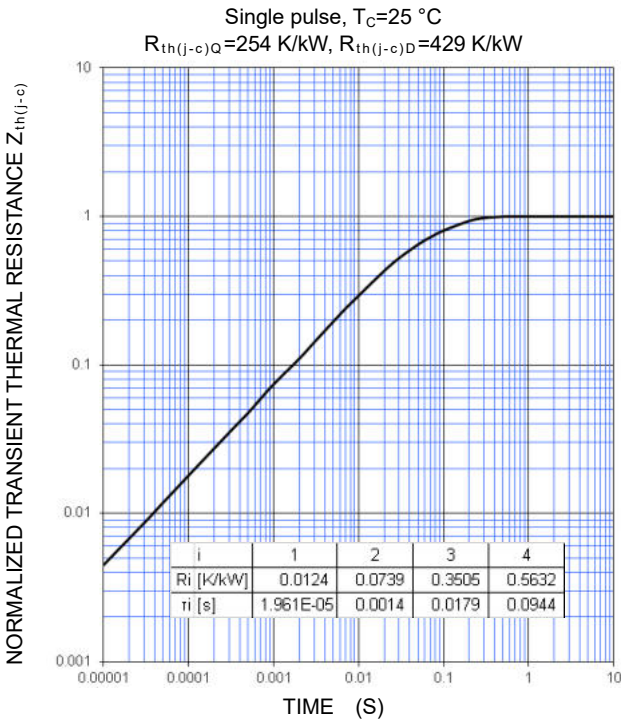
FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE CHARACTERISTICS
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)



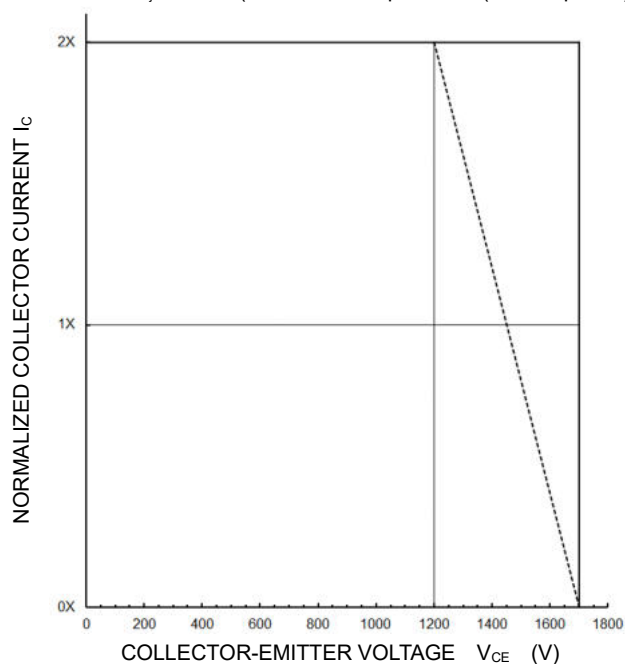
CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE

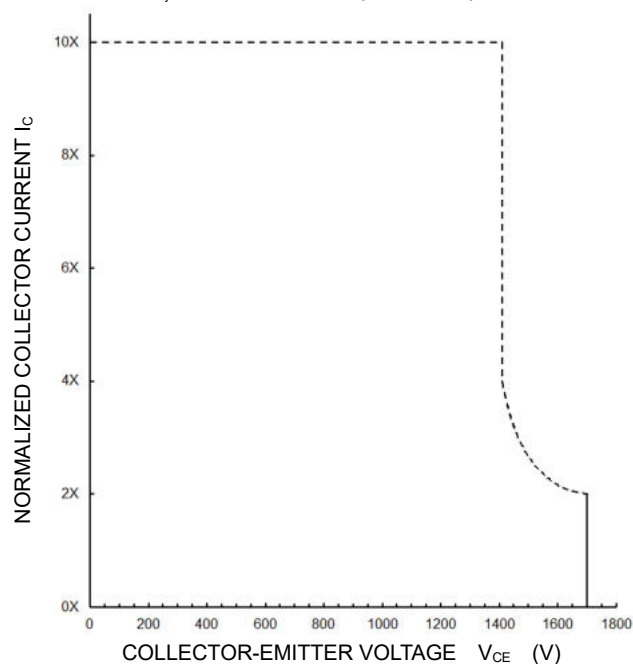
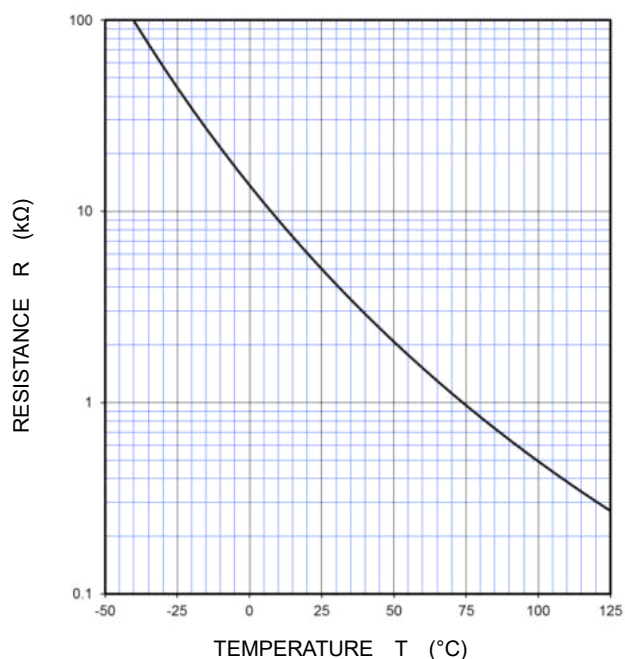
INSULATED TYPE

PERFORMANCE CURVES**INVERTER PART****TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 1200 \text{ V}$, $R_G = 0 \sim 91 \text{ } \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 —: $T_{vj} = 25 \sim 150 \text{ } ^\circ\text{C}$ (Normal load operations (Continuous))
 - - - - -: $T_{vj} = 175 \text{ } ^\circ\text{C}$ (Unusual load operations (Limited period))

**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 1200 \text{ V}$, $R_G = 0 \sim 91 \text{ } \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ } ^\circ\text{C}$, $t_W \leq 8 \text{ } \mu\text{s}$, Non-Repetitive

**NTC thermistor part****TEMPERATURE CHARACTERISTICS
(TYPICAL)**

Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

CM100TX-34T/CM100TXP-34T

HIGH POWER SWITCHING USE

INSULATED TYPE

Important Notice

The information contained in this datasheet shall in no event be regarded as a guarantee of conditions or characteristics. This product has to be used within its specified maximum ratings, and is subject to customer's compliance with any applicable legal requirement, norms and standards.

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